

## N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>	$Q_g$ (Typ.)
40	0.0025 at $V_{GS} = 10$ V	120	38 nC
	0.0028 at $V_{GS} = 6.5$ V	105	

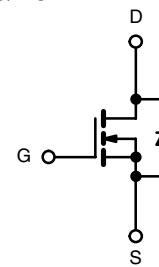
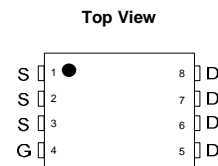
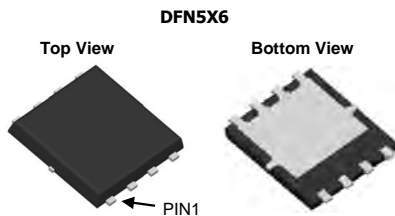
### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 %  $R_g$  Tested
- 100 % UIS Tested



### APPLICATIONS

- Synchronous Rectification
- Secondary Side DC/DC



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	40	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C)	$T_C = 25$ °C	$I_D$	120	A
	$T_C = 70$ °C		80	
	$T_A = 25$ °C		33 <sup>b, c</sup>	
	$T_A = 70$ °C		26 <sup>b, c</sup>	
Pulsed Drain Current		$I_{DM}$	360	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	$I_S$	100	
	$T_A = 25$ °C		4.9 <sup>b, c</sup>	
Single Pulse Avalanche Current	L = 0.1 mH	$I_{AS}$	40	mJ
Single Pulse Avalanche Energy		$E_{AS}$	80	
Maximum Power Dissipation	$T_C = 25$ °C	$P_D$	83	W
	$T_C = 70$ °C		53	
	$T_A = 25$ °C		5.4 <sup>b, c</sup>	
	$T_A = 70$ °C		3.4 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>			260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, f</sup>	$t \leq 10$ s	$R_{thJA}$	18	23	°C/W
Maximum Junction-to-Case (Drain)	Steady State	$R_{thJC}$	1.0	1.5	

Notes:

- Based on  $T_C = 25$  °C.
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$  s.
- Maximum under steady state conditions is 90 °C/W.
- Calculated based on maximum junction temperature. Package limitation current is 80 A.

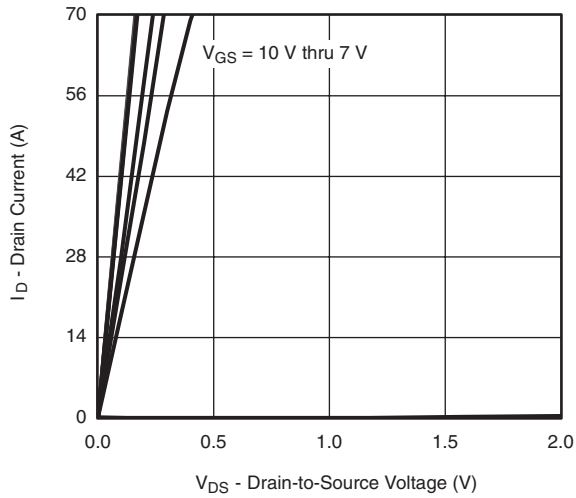
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		43		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-6		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0		4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	100			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.0025		$\Omega$
		$V_{GS} = 6.5\text{ V}, I_D = 20\text{ A}$		0.0029		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		102		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		4750		pF
Output Capacitance	$C_{oss}$			610		
Reverse Transfer Capacitance	$C_{rss}$			275		
Total Gate Charge	$Q_g$	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		78	117	nC
				38	57	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 20\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		13		
Gate-Drain Charge	$Q_{gd}$			11		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	0.2	0.7	1.4	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 2\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		14	25	ns
Rise Time	$t_r$			9	18	
Turn-Off Delay Time	$t_{d(off)}$			41	65	
Fall Time	$t_f$			9	18	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 2\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		33	42	
Rise Time	$t_r$			22	35	
Turn-Off Delay Time	$t_{d(off)}$			42	65	
Fall Time	$t_f$			13	25	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$		50		A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$			60		
Body Diode Voltage	$V_{SD}$	$I_S = 5\text{ A}$		0.75	1.1	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		40	60	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			48	72	nC
Reverse Recovery Fall Time	$t_a$			24		ns
Reverse Recovery Rise Time	$t_b$			16		

Notes:

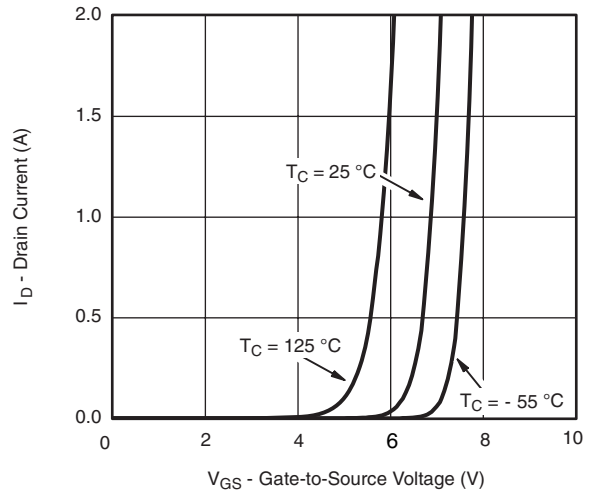
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

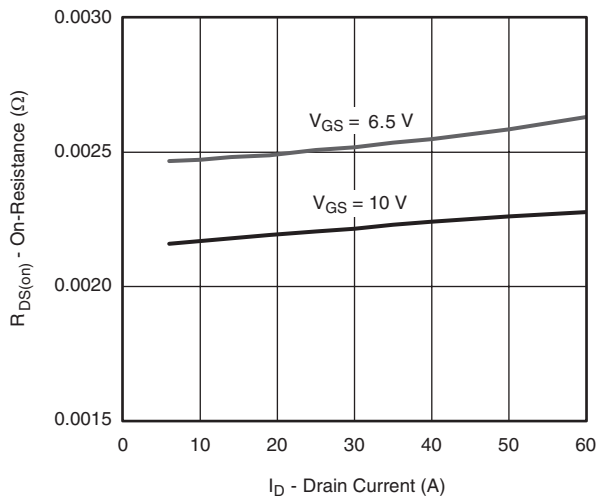
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



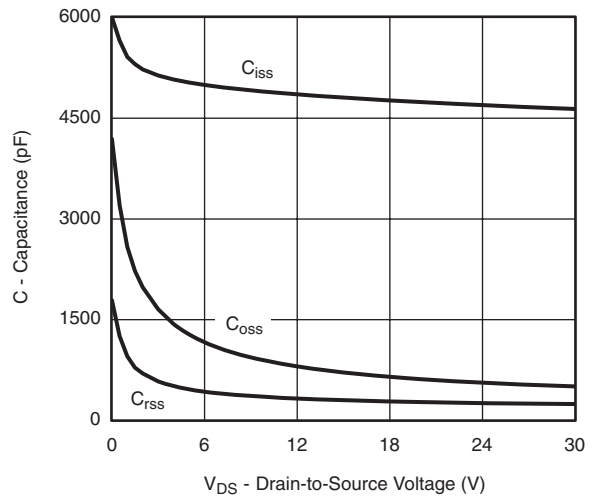
**Output Characteristics**



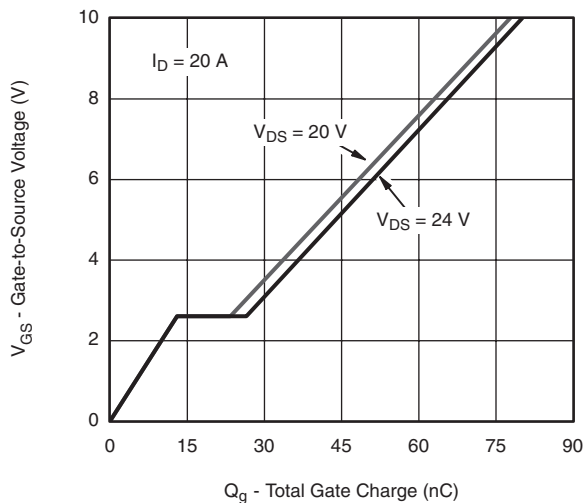
**Transfer Characteristics**



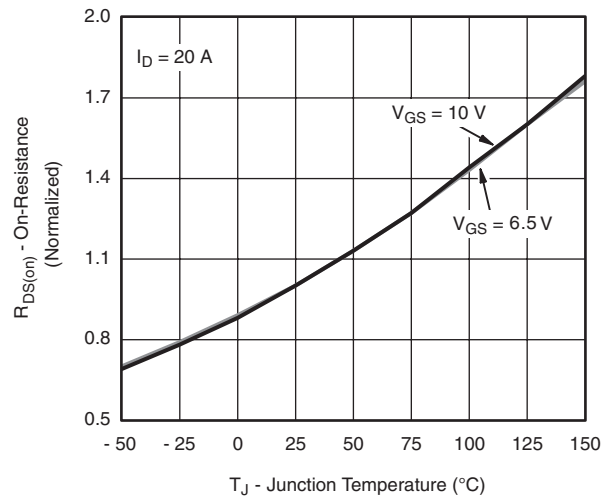
**On-Resistance vs. Drain Current**



**Capacitance**

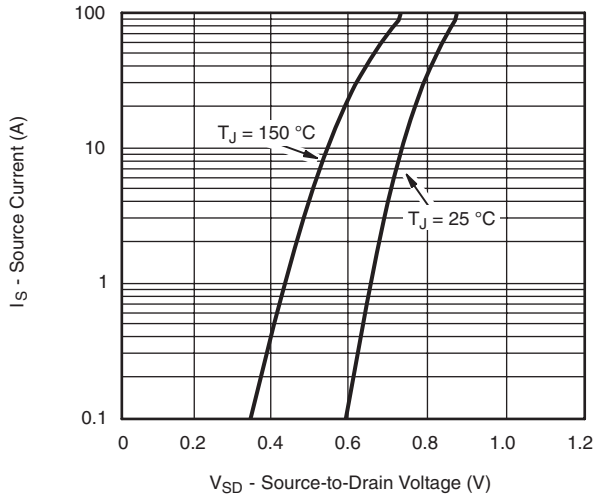


**Gate Charge**

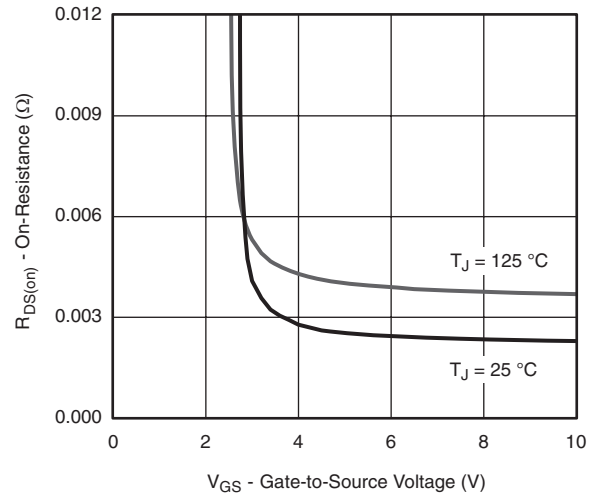


**On-Resistance vs. Junction Temperature**

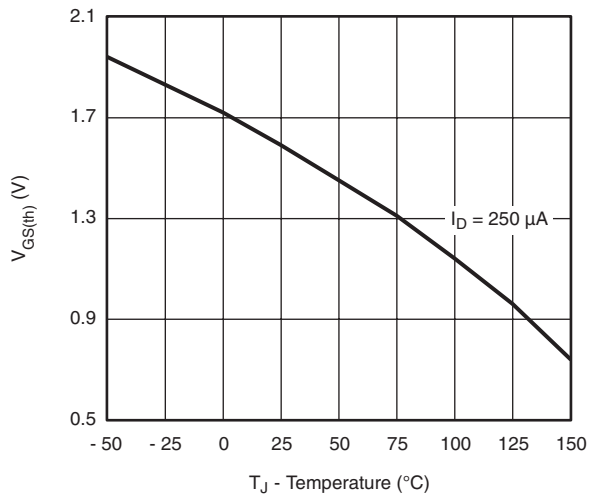
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



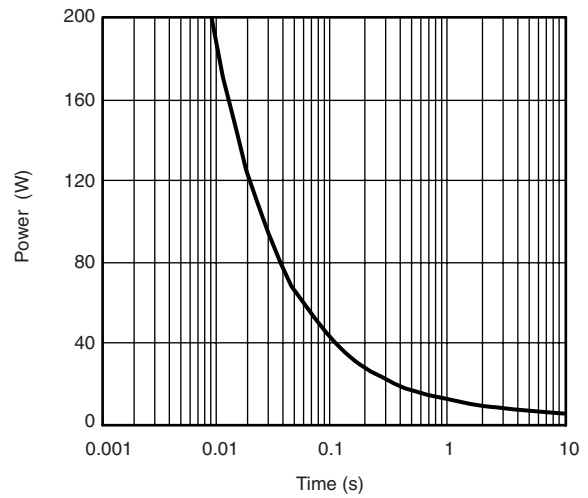
**Source-Drain Diode Forward Voltage**



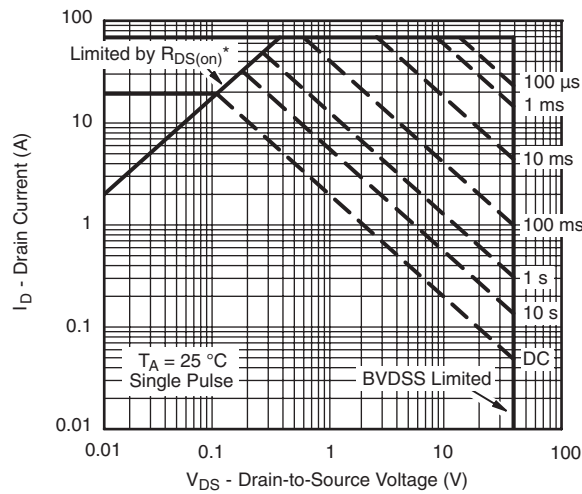
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



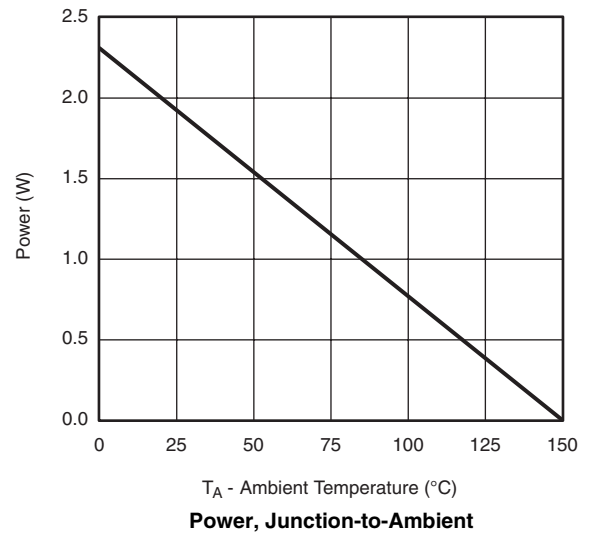
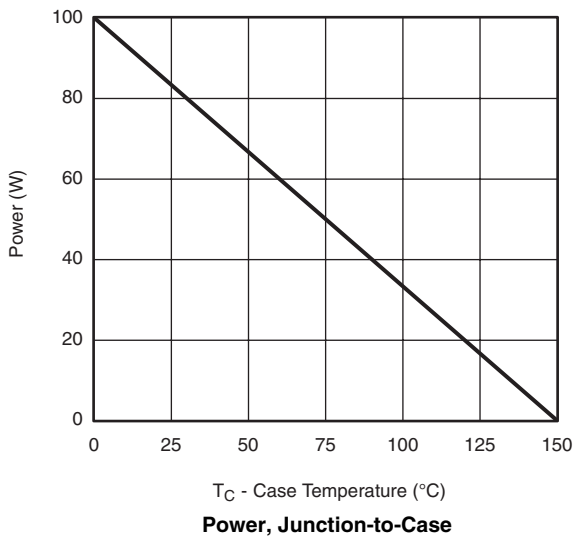
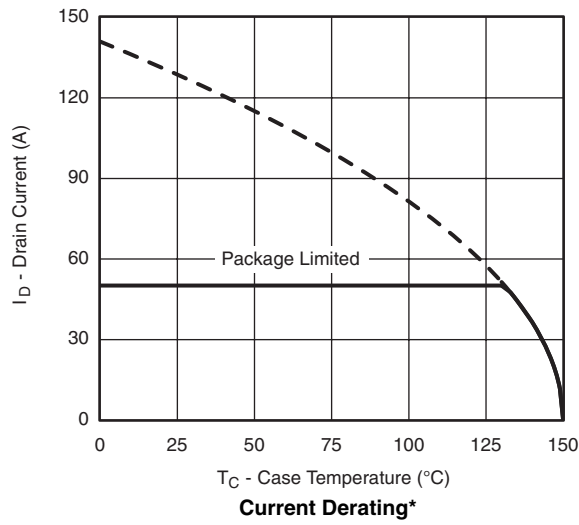
**Single Pulse Power, Junction-to-Ambient**



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

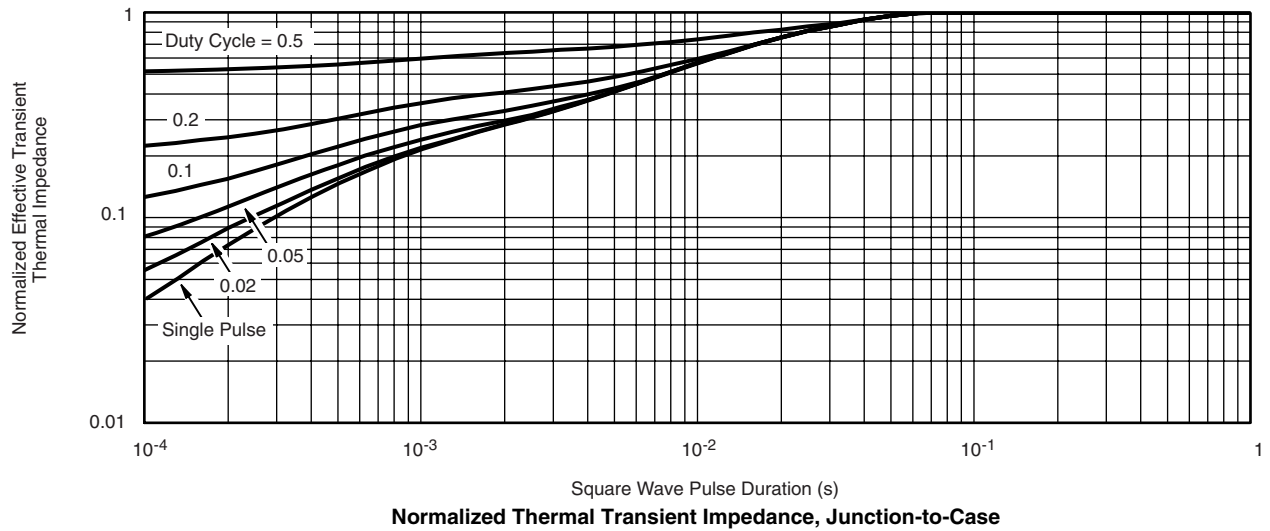
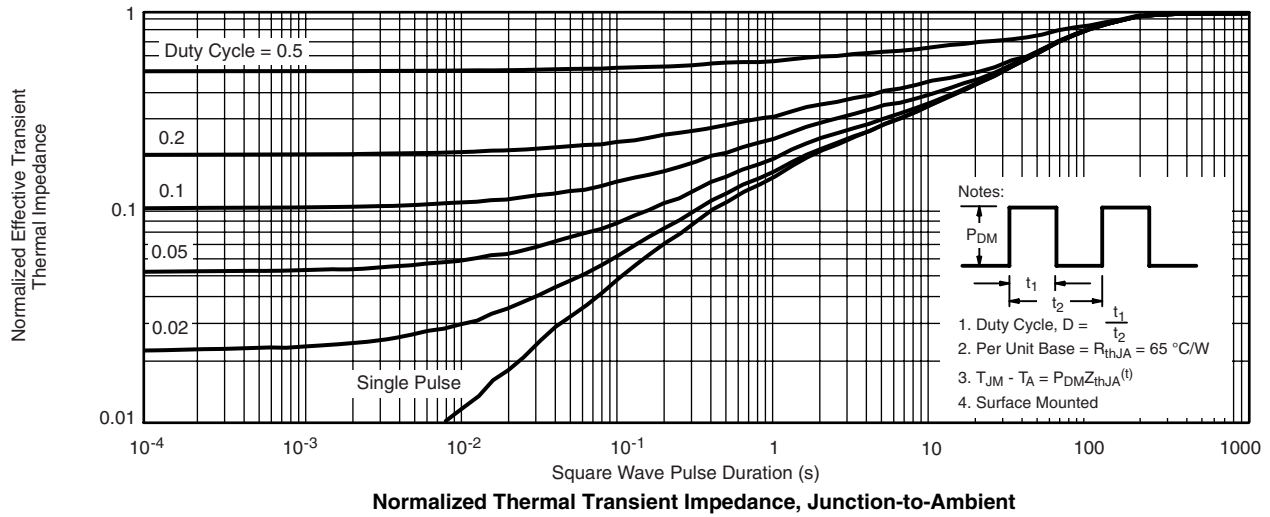
**Safe Operating Area, Junction-to-Ambient**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

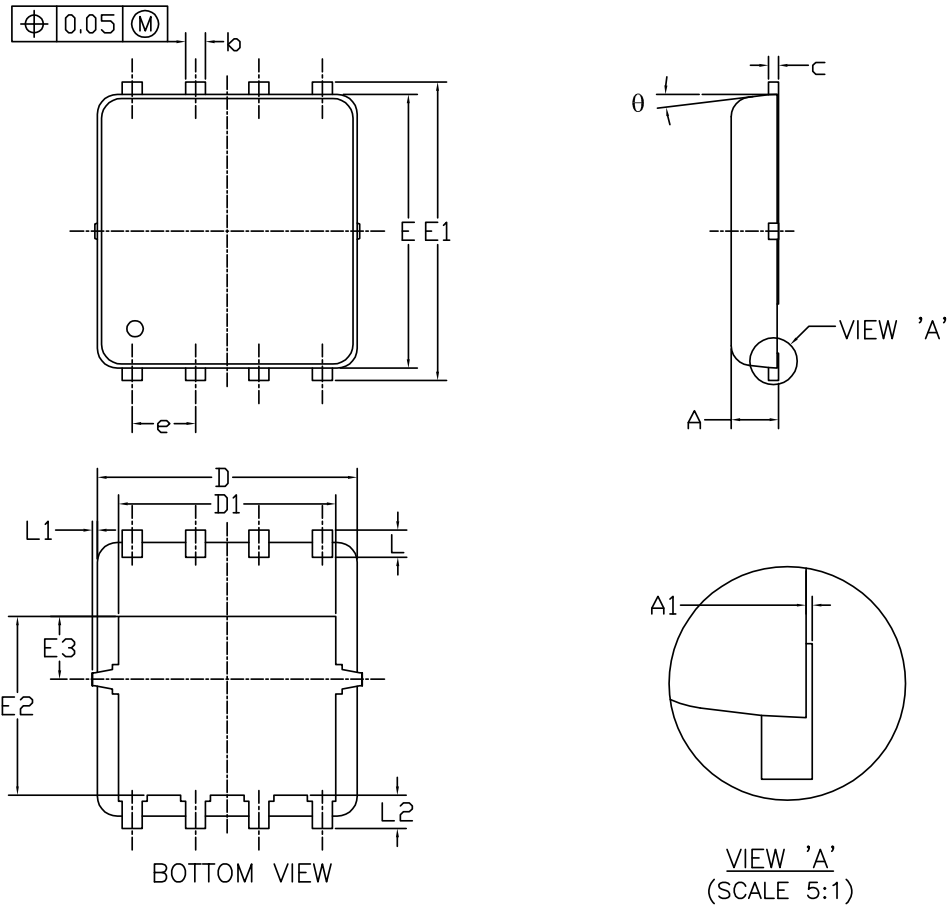


\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

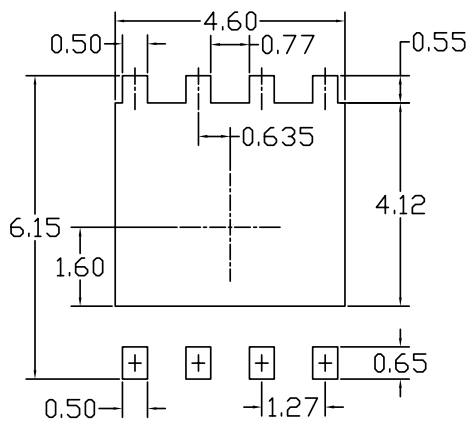
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



DFN5x6\_8L\_EP1\_P PACKAGE OUTLIN



RECOMMENDED LAND PATTERN



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.10	5.20	5.30	0.201	0.205	0.209
D1	4.25	4.35	4.45	0.167	0.171	0.175
E	5.45	5.55	5.65	0.215	0.219	0.222
E1	5.95	6.05	6.15	0.234	0.238	0.242
E2	3.525	3.625	3.725	0.139	0.143	0.147
E3	1.175	1.275	1.375	0.046	0.050	0.054
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	---	0.15	0	---	0.006
L2	0.68 REF			0.027 REF		
$\theta$	0°	---	10°	0°	---	10°

NOTE

UNIT: mm

- PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.  
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
- CONTROLLING DIMENSION IS MILLIMETER.  
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

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